BTA208X-1000B



3Q Hi-Com Triac Rev. 03 — 24 January 2011

Product data sheet

1. **Product profile**

1.1 General description

Planar passivated high commutation three quadrant triac in a SOT186A "full pack" plastic package intended for use in circuits where very high blocking voltage, high static and dynamic dV/dt and high dl/dt can occur. This "series B" triac will commutate the full rated RMS current at the maximum rated junction temperature without the aid of a snubber.

1.2 Features and benefits

- 3Q technology for improved noise immunity
- High commutation capability with maximum false trigger immunity
- High immunity to false turn-on by dV/dt
- Isolated mounting base package
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only
- Very high voltage capability

1.3 Applications

- Compressor starting controls
- General purpose motor controls
- Reversing induction motor controls e.g. vertical axis washing machines

1.4 Quick reference data

Table 1. Quick reference data

Parameter	Conditions	Min	Тур	Max	Unit
repetitive peak off-state voltage		-	-	1000	V
non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25$ °C; $t_p = 20$ ms; see <u>Figure 4</u> ; see <u>Figure 5</u>	-	-	65	Α
RMS on-state current	full sine wave; $T_h \le 73$ °C; see <u>Figure 3</u> ; see <u>Figure 1</u> ; see <u>Figure 2</u>	-	-	8	Α
acteristics					
gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{\text{Figure 7}}$	2	18	50	mA
	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{}$	2	21	50	mA
	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2\text{- G-;}$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{}$	2	34	50	mA
	repetitive peak off-state voltage non-repetitive peak on-state current RMS on-state current	repetitive peak off-state voltage $ \begin{array}{ll} \text{non-repetitive peak} \\ \text{on-state current} \end{array} \qquad \begin{array}{ll} \text{full sine wave; $T_{j(init)} = 25 \ ^{\circ}$C;} \\ \text{t}_{p} = 20 \ \text{ms; see } \underline{\text{Figure 4}}; \\ \text{see } \underline{\text{Figure 5}} \end{array} $ RMS on-state current $ \begin{array}{ll} \text{full sine wave; $T_{h} \leq 73 \ ^{\circ}$C;} \\ \text{see } \underline{\text{Figure 3}}; \text{ see } \underline{\text{Figure 1}}; \\ \text{see } \underline{\text{Figure 2}} \end{array} $ $ \begin{array}{ll} \text{acteristics} \\ \text{gate trigger current} \end{array} \qquad \begin{array}{ll} V_{D} = 12 \ \text{V; $I_{T} = 0.1 \ \text{A; $T2$+ G+;}} \\ V_{D} = 12 \ \text{V; $I_{T} = 0.1 \ \text{A; $T2$+ G-;}} \\ V_{D} = 12 \ \text{V; $I_{T} = 0.1 \ \text{A; $T2$- G-;}} \end{array} $	repetitive peak off-state voltage	repetitive peak off-state voltage $\begin{array}{cccccccccccccccccccccccccccccccccccc$	repetitive peak off-state voltage $ \begin{array}{ccccccccccccccccccccccccccccccccccc$



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		N I
2	T2	main terminal 2	mb	T2T1
3	G	gate		sym051
mb	n.c.	mounting base; isolated	1 2 3	
			SOT186A (TO-220F)	

3. Ordering information

Table 3. Ordering information

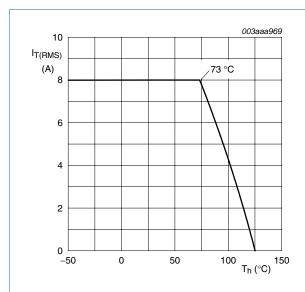
Type number	Package		
	Name	Description	Version
BTA208X-1000B	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A

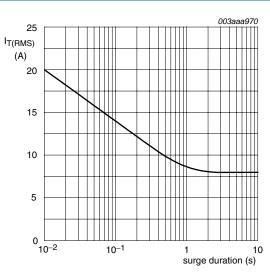
4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	1000	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_h \le 73$ °C; see <u>Figure 3</u> ; see <u>Figure 1</u> ; see <u>Figure 2</u>	-	8	Α
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; see Figure 4; see Figure 5	-	65	Α
		full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 16.7 \text{ ms}$	-	71	Α
I ² t	I2t for fusing	$t_p = 10 \text{ ms}$; sine-wave pulse	-	21	A ² s
dI _T /dt	rate of rise of on-state current	$I_T = 0.2 \text{ A}$; $I_G = 0.2 \text{ A}$; $dI_G/dt = 0.2 \text{ A}/\mu\text{s}$	-	100	A/µs
I _{GM}	peak gate current		-	2	Α
V_{GM}	peak gate voltage		-	5	V
P _{GM}	peak gate power		-	5	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C





 $f = 50 \text{ Hz}; T_h = 73 \,^{\circ}C$

Fig 1. RMS on-state current as a function of heatsink temperature; maximum values

Fig 2. RMS on-state current as a function of surge duration; maximum values

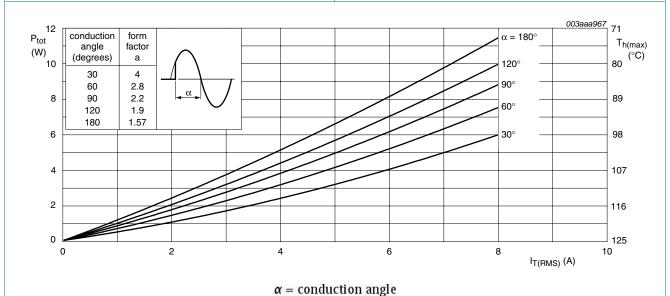


Fig 3. Total power dissipation as a function of RMS on-state current; maximum values

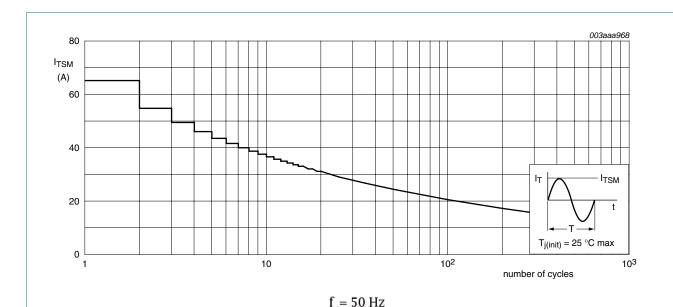
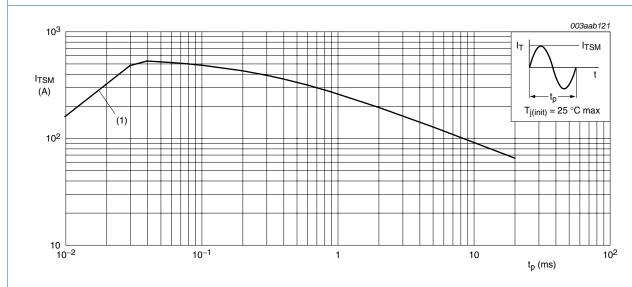


Fig 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



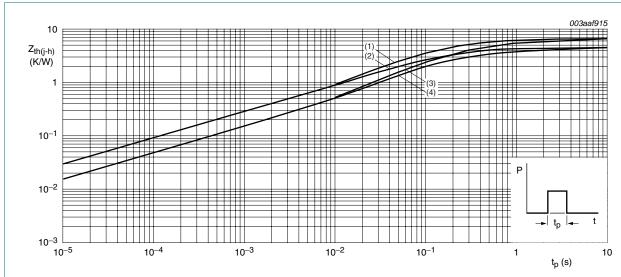
 $t_p \leq 20 \text{ ms}; (1) dI_T/dt \text{ limit}$

Fig 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	full cycle or half cycle; with heatsink compound; see Figure 6	-	-	4.5	K/W
		full cycle or half cycle; without heatsink compound; see Figure 6	-	-	6.5	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	55	-	K/W



- (1) Unidirectional (half cycle) without heatsink compound
- (2) Unidirectional (half cycle) with heatsink compound
- (3) Bidirectional (full cycle) without heatsink compound
- (4) Bidirectional (full cycle) with heatsink compound

Fig 6. Transient thermal impedance from junction to heatsink as a function of pulse duration

6. Isolation characteristics

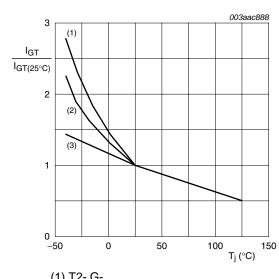
Table 6. Isolation characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{\text{isol}(\text{RMS})}$	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free ; 50 Hz \leq f \leq 60 Hz; RH \leq 65 %; T _h = 25 °C	-	-	2500	V
C _{isol}	isolation capacitance	from main terminal 2 to external heatsink ; $f = 1 \text{ MHz}$; $T_h = 25 ^{\circ}\text{C}$	-	10	-	pF

7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+G+; T_j = 25 ^{\circ}\text{C};$ see Figure 7	2	18	50	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G-; T_j = 25 ^{\circ}\text{C};$ see Figure 7	2	21	50	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- G-; T_j = 25 °C;$ see Figure 7	2	34	50	mA
lL	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+G+; T_j = 25 ^{\circ}\text{C};$ see Figure 8	-	31	60	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-; T_j = 25 ^{\circ}\text{C};$ see Figure 8	-	34	90	mA
	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-}; T_j = 25 \text{ °C};$ see Figure 8	-	30	60	mA	
I _H	holding current	$V_D = 12 \text{ V; } T_j = 25 \text{ °C; see } \frac{\text{Figure 9}}{}$	-	31	60	mΑ
V _T	on-state voltage	$I_T = 10 \text{ A}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 10}{}$	-	1.3	1.65	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ see Figure 11	-	0.7	1.5	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C}$	0.25	0.4	-	V
I _D	off-state current	$V_D = 1000 \text{ V}; T_j = 125 \text{ °C}$	-	0.1	0.5	mΑ
Dynamic ch	aracteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 670 V; T_j = 125 °C; exponential waveform; gate open circuit	1000	4000	-	V/µs
dI _{com} /dt	rate of change of commutating current	$V_D = 400 \text{ V}; T_j = 125 \text{ °C}; I_{T(RMS)} = 8 \text{ A};$ $dV_{com}/dt = 20 \text{ V/}\mu\text{s}; \text{ gate open circuit};$ snubberless condition; see Figure 12	15	38	-	A/ms



- (1) T2- G-
- (2) T2+ G-
- (3) T2+ G+

Normalized gate trigger current as a function of Fig 7. junction temperature

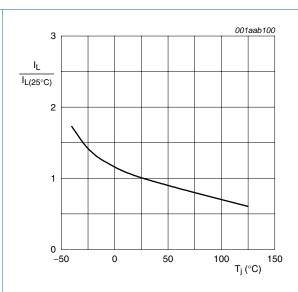
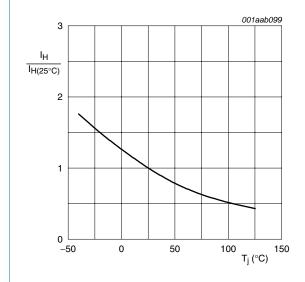
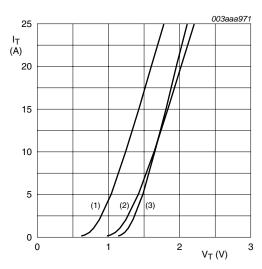


Fig 8. Normalized latching current as a function of junction temperature



Normalized holding current as a function of Fig 9. junction temperature



Vo = 1.264 V; Rs = 0.0378 Ω

- (1) Tj = 125 °C; typical values
- (2) Tj = 125 °C; maximum values
- (3) Tj = 25 °C; maximum values

Fig 10. On-state current as a function of on-state voltage

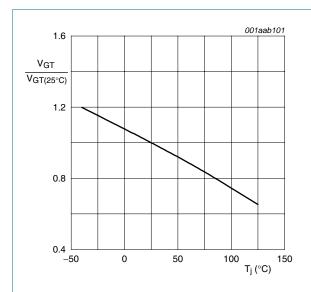


Fig 11. Normalized gate trigger voltage as a function of junction temperature

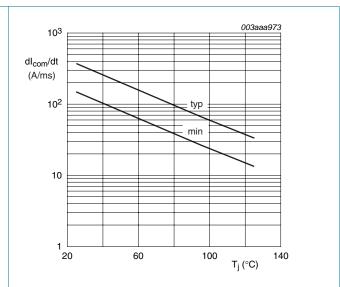
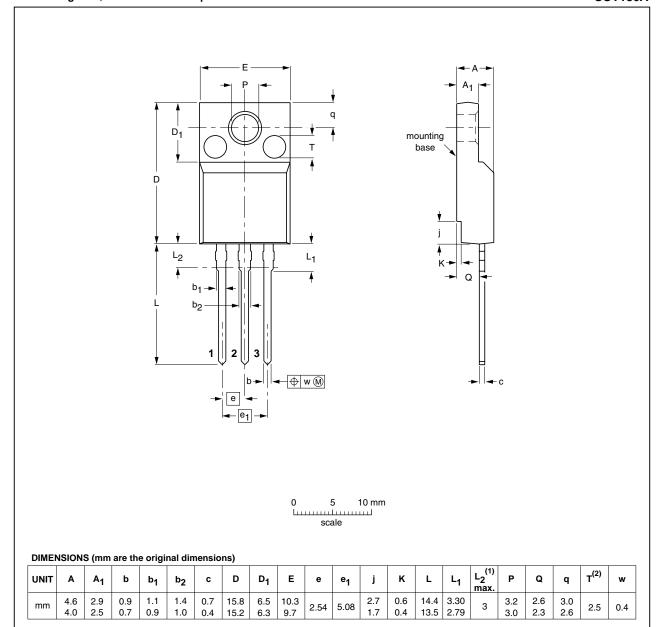


Fig 12. Rate of change of commutating current as a function of junction temperature; typical and minimum values

8. Package outline

Plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 'full pack'

SOT186A



Notes

- 1. Terminal dimensions within this zone are uncontrolled.
- 2. Both recesses are \varnothing 2.5 \times 0.8 max. depth

	REFERENCES EUROPE		EUROPEAN	ISSUE DATE	
IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
	3-lead TO-220F				-02-04-09 06-02-14
	IEC	IEC JEDEC	IEC JEDEC JEITA	IEC JEDEC JEITA	IEC JEDEC JEITA PROJECTION

Fig 13. Package outline SOT186A (TO-220F)

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9. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BTA208X-1000B v.3	20110124	Product data sheet	-	BTA208X-1000B v.2
Modifications:	 Various changes 	to content.		
BTA208X-1000B v.2	20101109	Product data sheet	-	BTA208X-1000B v.1

10. Legal information

10.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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